

ABSTRACT

A semiconductor device includes a lower wiring structure disposed within a lower interlayer insulating film, and the lower wiring structure including a lower barrier film and a lower filling film disposed on the lower barrier film, a wiring isolation pattern extending along an upper surface of the lower interlayer insulating film, in contact with the lower interlayer insulating film, and the wiring isolation pattern including aluminum silicate, an upper interlayer insulating film disposed on the lower wiring structure and the wiring isolation pattern, and an upper wiring structure disposed within the upper interlayer insulating film and connected to the lower wiring structure.

FIG. 3